

<b>PCN Number:</b>	20241217007.1	<b>PCN Date:</b>	December 18, 2024		
<b>Title:</b>	Qualification of FFAB using qualified Process Technology, Die Revision, Assembly site (FMX & MLA), alternate BOM qualification & Datasheet changes for select devices				
<b>Customer Contact:</b>	Change Management Team	<b>Dept:</b>	Quality Services		
<b>Proposed 1<sup>st</sup> Ship Date:</b>	March 18, 2025	<b>Sample requests accepted until:</b>	January 17, 2025*		
<b>*Sample requests received after January 17, 2025 will not be supported.</b>					
<b>Change Type:</b>					
<input checked="" type="checkbox"/>	Assembly Site	<input checked="" type="checkbox"/>	Design		
<input checked="" type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Data Sheet		
<input checked="" type="checkbox"/>	Assembly Materials	<input type="checkbox"/>	Part number change		
<input type="checkbox"/>	Mechanical Specification	<input type="checkbox"/>	Test Site		
<input checked="" type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process		
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Material		
<input type="checkbox"/>		<input type="checkbox"/>	Wafer Bump Process		
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Site		
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Material		
<input checked="" type="checkbox"/>		<input checked="" type="checkbox"/>	Wafer Fab Process		
<b>PCN Details</b>					
<b>Description of Change:</b>					
Texas Instruments is pleased to announce the qualification of its FFAB fabrication facility as an additional Wafer Fab option for the devices listed below as well as new assembly site (FMX & MLA) and BOM options:					
<b>Current Fab Site</b>			<b>Additional Fab Site</b>		
<b>Fab Site</b>	<b>Process</b>	<b>Wafer Diameter</b>	<b>Fab Site</b>	<b>Process</b>	<b>Wafer Diameter</b>
DL-LIN	BICOM	150 mm	FR-BIP-1	BICOMHD	200 mm
The die was also changed as a result of the process change.					
Construction differences are as follows:					
<b>Group 1 BOM Table (FFAB/Process migration, die change plus FMX as new Assembly site &amp; BOM update):</b>					
		TAI	<b>FMX</b>		
Bond wire composition, diameter		Au, 0.96 mil	<b>Cu, 0.8 mil</b>		
Device Marking		Pin one stripe, TI Logo	<b>Pin one dot, TI letters</b>		
<b>Group 2 BOM Table (FFAB/Process migration, die change plus MLA as new Assembly site &amp; BOM update):</b>					
	ASESH	HNA	<b>MLA</b>		
Bond wire composition, diameter	Cu, 1.0 mil	Au, 1.0 mil	<b>Cu, 0.8 mil</b>		
Mold Compound	SID#EN2000515	SID#450179	<b>4211880</b>		
Mount Compound	SID#EY1000063	SID#400180	<b>4224795</b>		
Device Markint	Pin one dot	Pin one dot	<b>Pin one embossed</b>		
Datasheet updates are included below:					

**Changes from Revision H (September 2009) to Revision I (December 2024) Page**

• Updated the numbering format for tables, figures, and cross-references throughout the document.....	1
• Added the <i>Pin Configuration and Functions, Specifications, ESD Ratings, Recommended Operating Conditions, Thermal Information, Detailed Description, Overview, Functional Block Diagram, Device Functional Modes, Application and Implementation, Typical Applications, Power Supply Recommendations, Layout, Layout Guidelines, Thermal Considerations, Device and Documentation Support, and Mechanical, Packaging, and Orderable Information</i> sections.....	1
• Updated table note 1 on <i>Absolute Maximum Ratings</i> to add additional clarification.....	4
• Deleted THS3001HV from <i>Absolute Maximum Ratings</i> .....	4
• Deleted THS3001HV from <i>Recommended Operating Conditions</i> .....	4
• Updated <i>Recommended Operating Conditions</i> with nominal values.....	4
• Changed V <sub>ss</sub> to V <sub>cc</sub> in <i>Recommended Operating Conditions</i> to maintain consistency with <i>Absolute Maximum Ratings</i> .....	4
• Moved <i>Operating Characteristics</i> to be included in <i>Electrical Characteristics</i> .....	5
• Changed bandwidth for 0.1dB flatness in <i>Electrical Characteristics</i> from 85MHz (5V) and 115MHz (15V) to 65MHz (5V) and 55MHz (15V).....	5
• Deleted differential gain and phase from <i>Electrical Characteristics</i> .....	5
• Deleted power supply operating range from <i>Electrical Characteristics</i> .....	5
• Deleted <i>Slew Rate vs Supply Voltage</i> from <i>Typical Characteristics</i> .....	7
• Deleted <i>Differential Gain and Phase Loading</i> from <i>Typical Characteristics</i> .....	7

The datasheet number will be changing.

Device Family	Change From:	Change To:
THS3001	SLOS217H	<b>SLOS217I</b>

These changes may be reviewed at the datasheet links provided.

<http://www.ti.com/product/THS3001>

Qual details are provided in the Qual Data Section.

**Reason for Change:**

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

**Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):**

None

**Impact on Environmental Ratings:**

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
<input checked="" type="checkbox"/> No Change			

**Changes to product identification resulting from this PCN:**
**Fab Site Information:**

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
DL-LIN	DLN	USA	Dallas
<b>FR-BIP-1</b>	<b>TID</b>	<b>DEU</b>	<b>Freising</b>

**Die Rev:****Current****New**

Die Rev [2P]	<b>Die Rev [2P]</b>
A	<b>A</b>

**Assembly Site Information:**

Assembly Site	Assembly Site Origin (22L)	Assembly Country Code (23L)	Assembly City
TI Taiwan	TAI	TWN	Chung Ho, New Taipei City
ASESH	ASH	CHN	Shanghai
HNA	HNT	THA	Ayutthaya
<b>TI Mexico</b>	<b>MEX</b>	<b>MEX</b>	<b>Aguascalientes</b>
<b>MLA</b>	<b>MLA</b>	<b>MYS</b>	<b>Kuala Lumpur</b>

Sample product shipping label (not actual product label):

**Product Affected:****Group 1 Device List (FFAB/Process migration, die change plus FMX as new Assembly site & BOM update)**

THS3001IDR

**Group 2 Device List (FFAB/Process migration, die change plus MLA as new Assembly site & BOM update)**

THS3001IDGNR

For alternate parts with similar or improved performance, please visit the product page on [TI.com](https://www.ti.com)



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Selective Disclosure

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: <a href="#">THS3001IDR</a>	QBS Process Reference: <a href="#">THS3491IDDAR</a>	QBS Package Reference: <a href="#">LM393BIDR</a>	QBS Package Reference: <a href="#">UCC28061DR</a>	QBS Package Reference: <a href="#">TCAN1043DQ1</a>	QBS Package Reference: <a href="#">MC33063ADR</a>	QBS Process Reference: <a href="#">THS3095DDAR</a>	QBS Process Reference: <a href="#">THS2630SDR</a>
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	3/231/0	3/231/0	3/230/0	-
UHAST	A3	Autoclave	121C/15psig	96 Hours	-	-	-	3/227/0	3/231/0	-	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0	-	-	3/231/0	3/231/0	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0	3/227/0	3/231/0	3/231/0	3/231/0	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	3/231/0	-	3/231/0	-	3/231/0	3/231/0	-
HTSL	A6	High Temperature Storage Life	175C	500 Hours	-	-	3/231/0	-	3/135/0	-	-	-
HTOL	B1	Life Test	125C	1000 Hours	-	-	3/231/0	-	3/231/0	1/77/0	-	-
HTOL	B1	Life Test	140C	480 Hours	-	-	-	-	-	-	-	1/77/0
HTOL	B1	Life Test	70C Vcc Max (self heating brings Tj up to 150C)	300 Hours	-	3/231/0	-	-	-	-	-	-

Type	#	Test Name	Condition	Duration	Qual Device: <a href="#">THS3001IDR</a>	QBS Process Reference: <a href="#">THS3491IDDAR</a>	QBS Package Reference: <a href="#">LM393BIDR</a>	QBS Package Reference: <a href="#">UCC28061DR</a>	QBS Package Reference: <a href="#">TCAN1043DQ1</a>	QBS Package Reference: <a href="#">MC33063ADR</a>	QBS Process Reference: <a href="#">THS3095DDAR</a>	QBS Process Reference: <a href="#">THS2630SDR</a>
ELFR	B2	Early Life Failure Rate	70C (self heating brings Tj up to 150C)	24 Hours	-	3/3000/0	-	-	-	-	-	-
ESD	E2	ESD CDM	-	1500 Volts	-	-	-	-	1/3/0	-	-	-
ESD	E2	ESD CDM	-	250 Volts	1/3/0	3/9/0	2/6/0	-	-	-	1/3/0	1/3/0
ESD	E2	ESD HBM	-	1000 Volts	1/3/0	3/9/0	2/6/0	-	-	-	1/3/0	1/3/0
ESD	E2	ESD HBM	-	4000 Volts	-	-	-	-	1/3/0	-	-	-
LU	E4	Latch-Up	Per JESD78	-	1/3/0	3/18/0	2/6/0	-	1/6/0	-	1/3/0	1/3/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	3/90/0	3/90/0	-	3/90/0	1/30/0	1/30/0	1/30/0
FTY	E6	Final Test Yield	-	-	-	-	1/Pass	-	-	-	-	1/Pass

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device THS3001IDR is qualified at MSL1 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2401-156



TI Information  
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## Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Name	Condition	Duration	Qual Device: <a href="#">THS3001IDGNR</a>	QBS Product Reference: <a href="#">THS3001IDR</a>	QBS Package Reference: <a href="#">OPA2828IDGNR</a>	QBS Process Reference: <a href="#">THS3095DDAR</a>	QBS Package Reference: <a href="#">THS3091IDGNR</a>	QBS Process Reference: <a href="#">THS2630SDR</a>
HAST	A2	Biased HAST	130C/85%RH	96 Hours	-	-	-	3/230/0	-	-
HAST	A2	Temperature Humidity Bias	85C/85%RH	1000 Hours	-	-	3/230/0	-	-	-
UHAST	A3	Unbiased HAST	130C/85%RH	96 Hours	-	-	3/231/0	3/231/0	1/77/0	-
TC	A4	Temperature Cycle	-65C/150C	500 Cycles	-	-	3/231/0	3/231/0	1/77/0	-
HTSL	A6	High Temperature Storage Life	150C	1000 Hours	-	-	3/231/0	-	-	-
HTSL	A6	High Temperature Storage Life	170C	420 Hours	-	-	-	3/231/0	-	-
HTOL	B1	Life Test	115C <sup>1</sup>	300 Hours	-	-	1/76/0	-	-	-
HTOL	B1	Life Test	140C	480 Hours	-	-	-	-	-	1/77/0

Type	#	Test Name	Condition	Duration	Qual Device: <a href="#">THS3001IDGNR</a>	QBS Product Reference: <a href="#">THS3001IDR</a>	QBS Package Reference: <a href="#">OPA2828IDGNR</a>	QBS Process Reference: <a href="#">THS3095DDAR</a>	QBS Package Reference: <a href="#">THS3091IDGNR</a>	QBS Process Reference: <a href="#">THS2630SDR</a>
SD	C3	PB-Free Solderability	Precondition w.155C Dry Bake (4 hrs +/- 15 minutes); PB-Free Solder;	-	-	-	1/22/0	-	-	-
PD	C4	Physical Dimensions	(per mechanical drawing)	-	-	-	3/15/0	-	-	-
ESD	E2	ESD CDM	-	250 Volts	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
ESD	E2	ESD HBM	-	1000 Volts	-	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
LU	E4	Latch-Up	Per JESD78	-	-	1/3/0	1/3/0	1/3/0	1/3/0	1/3/0
CHAR	E5	Electrical Characterization	Per Datasheet Parameters	-	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0	1/30/0

- QBS: Qual By Similarity, also known as Generic Data
- Qual Device THS3001IDGNR is qualified at MSL2 260C

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2402-005

[1] Tj=150C

For questions regarding this notice, e-mails can be sent to the Change Management team or your local Field Sales Representative.

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